



SL210A SCHOTTKY RECTIFIER

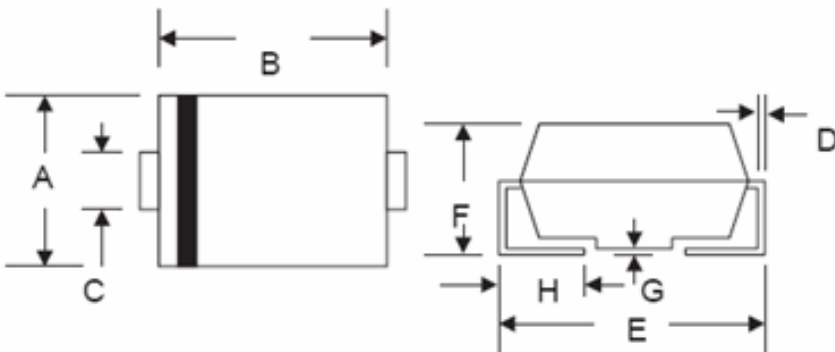
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

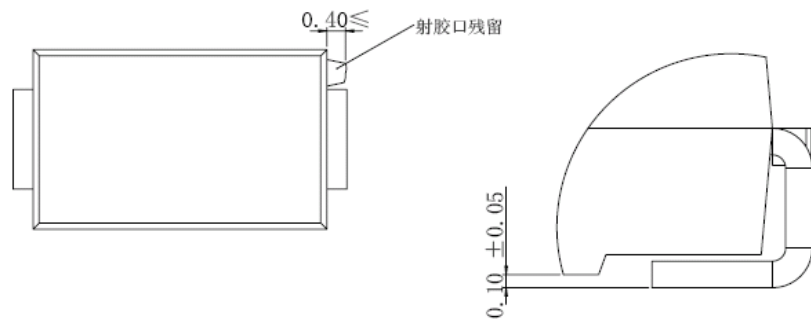
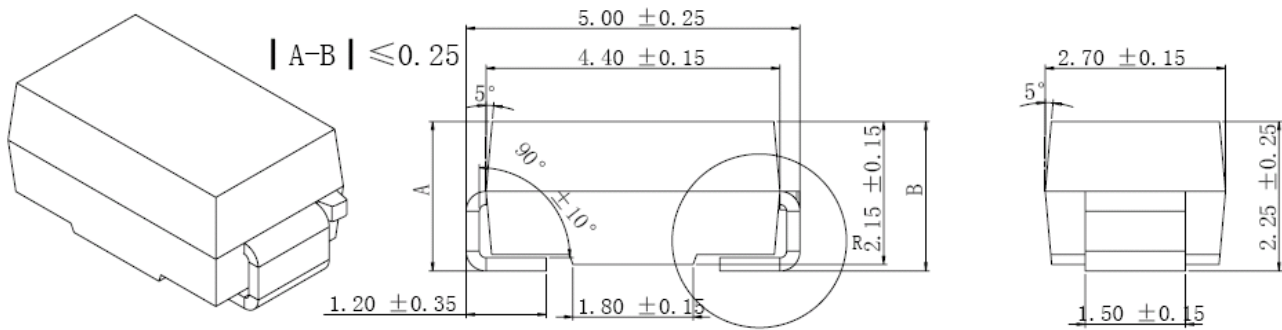
- 150°C TJ operation Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



SMA/DO-214AC				
Dim	Min	Max	Min	Max
A	2.50	2.90	0.098	0.114
B	4.00	4.60	0.157	0.181
C	1.40	1.60	0.055	0.063
D	0.152	0.305	0.006	0.012
E	4.80	5.28	0.189	0.208
F	2.00	2.44	0.079	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060
	In mm		In inch	

OPTION 1



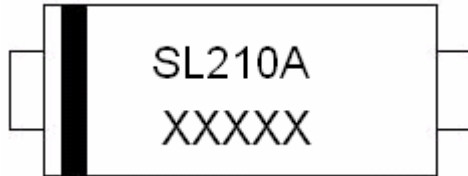
OPTION 2(JK)

SMA



Marking Diagram:

Where XXXXX is YYWWL



SL = Device Type
2 = Forward Current (2A)
10 = Reverse Voltage (100V)
A = Package type
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SL210A	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 115^\circ C$, rectangular wave form	2	A
peak one cycle Non-repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	70	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop *	V_{F1}	@ 2A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.78	V
	V_{F2}	@ 2A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.68	V
Reverse Current *	I_{R1}	@ $V_R = \text{rated VR}$ $T_J = 25\text{ }^\circ\text{C}$	0.1	mA
	I_{R2}	@ $V_R = \text{rated VR}$ $T_J = 100\text{ }^\circ\text{C}$	2.0	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	200	pF

* Pulse Width < 300 μ s, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Lead	$R_{\theta JL}$	-	17	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	-	75	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.11	g
Case Style	SMA			

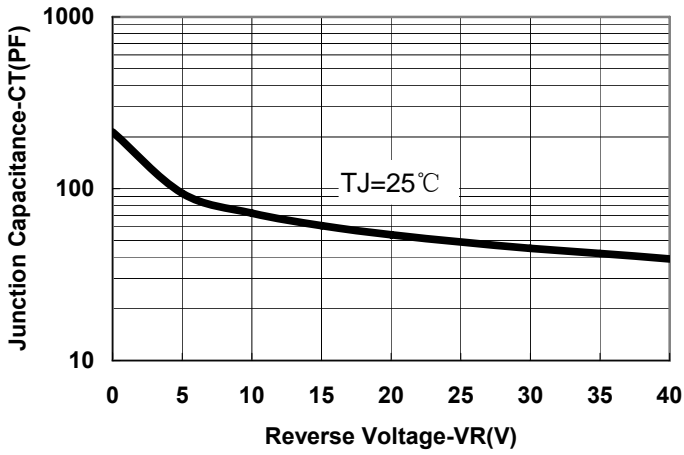


Fig.1-Typical Junction Capacitance Vs. Reverse Voltage

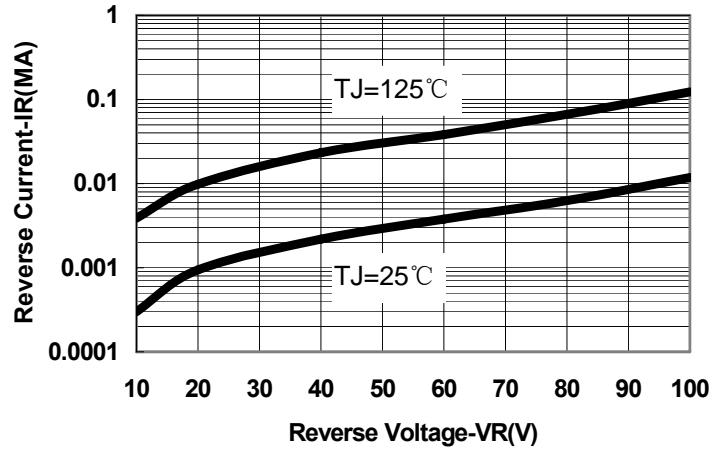


Fig.2-Typical Values Of Reverse Current Vs. Reverse Voltage

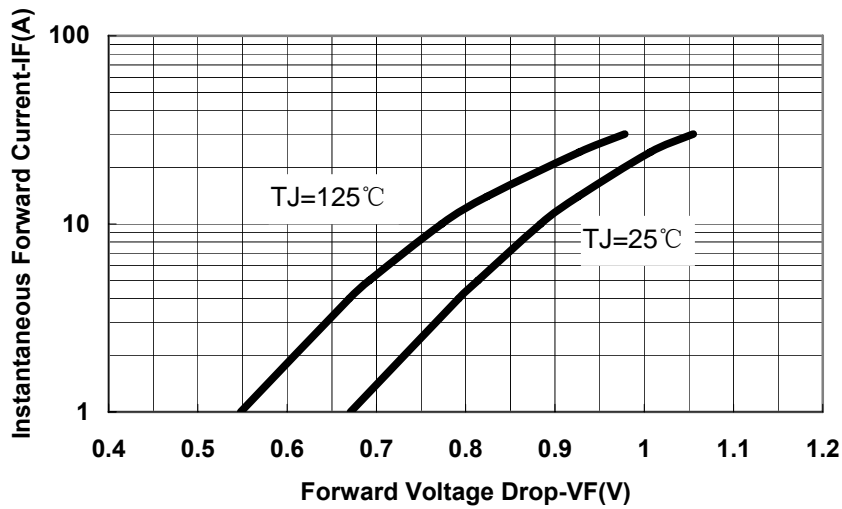


Fig.3-Typical Forward Voltage Drop Characteristics



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